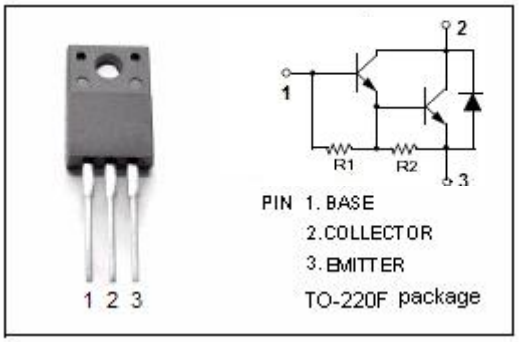
isc Silicon NPN Darlington Power Transistor KTD1414

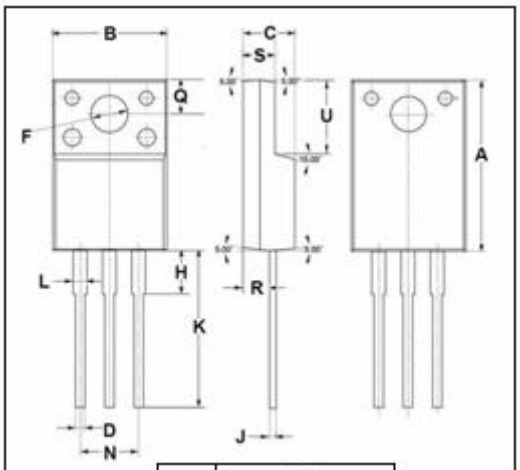
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 80V(Min)
- Collector-Emitter Saturation Voltage-
  : $V_{CE(sat)}$= 1.5V(Max) @I_C= 3A
- High DC Current Gain
  : h_{FE}= 2000(Min) @ I_C= 1A, V_{CE}= 2V
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Switching applications
- Hammer driver,pulse motor driver applications
- Power amplifier applications.



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 6mA			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 6mA			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			20	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			2.5	mA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 2V	2000			
h_{FE-2}	DC Current Gain	I_C= 3A; V_{CE}= 2V	1000			